

F.E.C. Semiconductor

II. Schottky Rectifier

High-Voltage Schottky Diodes

MBR20200/MBR20200F

■ Productor Character

- Half Bridge Rectified、Common Cathode Structure.
- Multilayer Metal -Silicon Potential Structure.
- Beautiful High Temperature Character.
- Have Over Voltage protect loop, high reliability.
- RoHs Product.

TO-220AB



■ Primary Use

- Low Voltage High Frequency Switching Power Supply.
- Low Voltage High Frequency Invers Circuit.
- Low Voltage Continued Circuit and Protection Circuit.

ITO-220AB

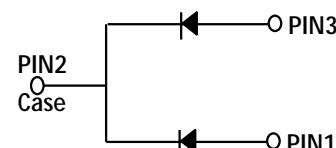


■ Summarize

- MBR20200/MBR20200F Device optimized for ultra-low forward voltage drop to maximize efficiency in Power Supply applications

Device Weight :

ITO-220AB-1.48g TO-220AB-1.96g



Absolute Maximum Ratings

Item	Symbol	Data	Unit
Maximal Inverted Repetitive Peak Voltage	VRRM	200	V
*Average Rectified Forward Current (Rated VR-20Khz Square Wave) - 50% duty cycle	IFAV	20	A
Typical Thermal Resistance (per leg)	R _{θJC}	2	°C/W
Package = TO-220AB		4	°C/W
Package = ITO-220AB			
Forward Peak Surge Current(Rated Load 8.3 Half Mssine Wave-According to JEDEC Method)	IFSM	150	A
Maximum Rate of Voltage Change (at Rated VR)	dv/dt	10000	V/uS
Peak Repetitive Reverse Surge Current (2uS-1Khz)	IRRM	1	A
Operating Junction Temperature	T _J	-40- +175	°C
Storage Temperature	T _{STG}	-40- +175	°C

Electricity Character

Item	Test Condition		TYP.	MAX.	Unit
IR	TJ =25°C	VR=VRRM		10	uA
	TJ =125°C			1	mA
VF	TJ =25°C	IF=10A		0.92	V
	TJ =125°C	IF=10A	0.66	0.72	V

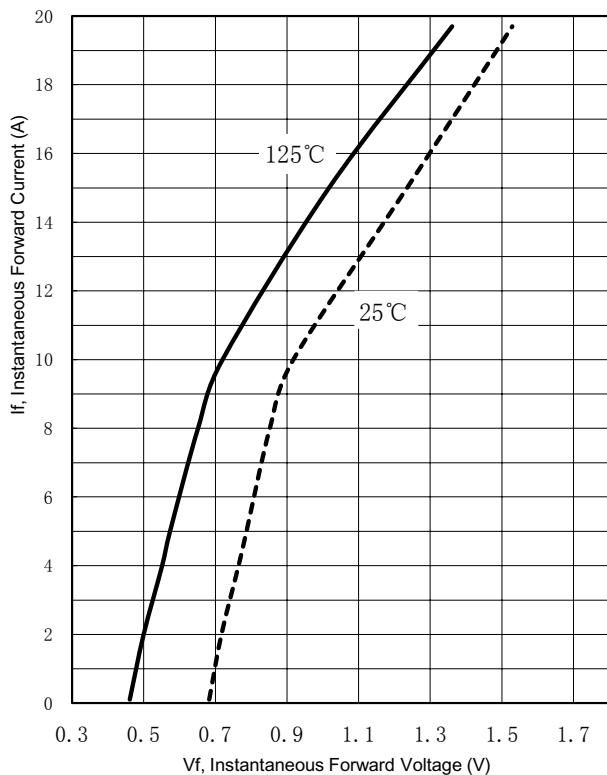
*IF(AV)= 10A×2

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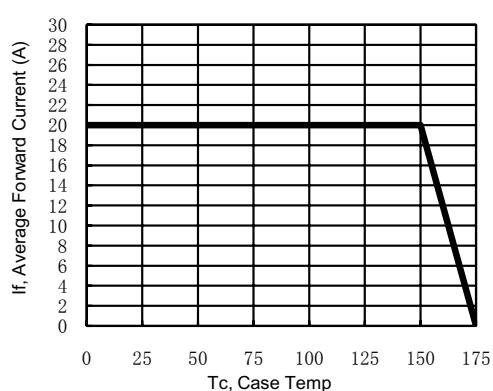
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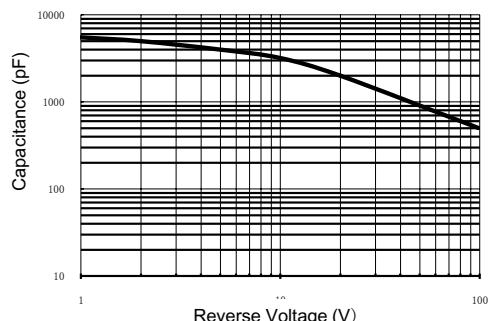
The forward voltage and forward current curve.



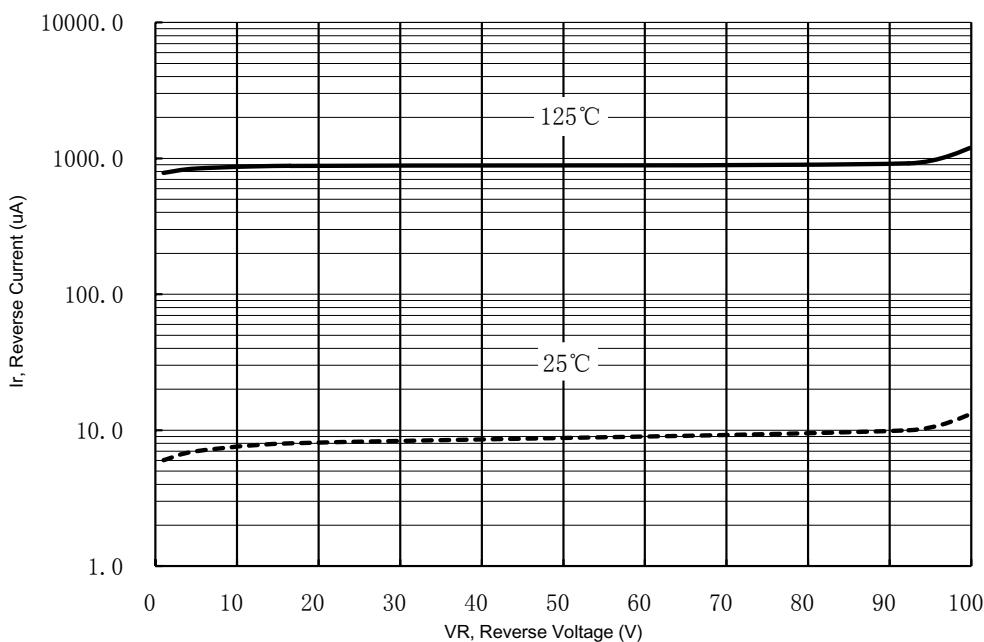
Current Derating Curve, Per Element



The crunode capacitance curve



The reverse leak current and the reverse voltage (single-device) curve.



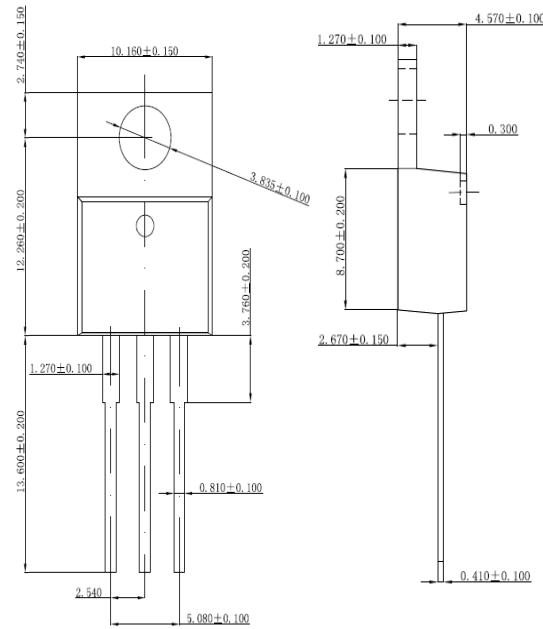
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Package Outline Dimensions millimeters

TO-220AB



ITO-220AB

